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978-1-107-40856-2 - Advances in GaN, GaAs, SiC and Related Alloys on Silicon Substrates:
Materials Research society Symposium proceedings: volume 1068

Editors: Tingkai Li, Joan M. Redwing, Michael Mastro, Edwin L. Piner and Armin Dadgar

Table of Contents

[More information](#)

CONTENTS

Preface	xiii
Acknowledgments	xv
Materials Research Society Symposium Proceedings.....	xvi

***GaN BASED ELECTRONIC DEVICE
AND SENSORS ON SILICON***

* GaN-on-Si HEMTs: From Device Technology to Product Insertion.....	3
Wayne Johnson, Sameer Singhal, Allen Hanson, Robert Therrien, Apurva Chaudhari, Walter Nagy, Pradeep Rajagopal, Quinn Martin, Todd Nichols, Andrew Edwards, John Roberts, Edwin Piner, Isik Kizilyalli, and Kevin Linthicum	
* GaN Electrochemical Probes and MEMS on Si.....	13
Ulrich Heinle, Peter Benkart, Ingo Daumiller, Mike Kunze, and Ertugrul Sönmez	
An Analytical Compact Direct-Current and Capacitance Model for AlGaIn/GaN High Electron Mobility Transistors	21
Miao Li, Xiaoxu Cheng, and Yan Wang	
Enhancement Mode GaN MOSFETs on Silicon Substrates with High Field-Effect Mobility.....	27
Hiroshi Kambayashi, Yuki Niiyama, Shinya Ootomo, Takehiko Nomura, Masayuki Iwami, Yoshihiro Satoh, Sadahiro Kato, and Seikoh Yoshida	
Integrated GaN/AlGaIn/GaN HEMTs with Precisely Controlled Resistance on Silicon Substrate Fabricated by Ion Implantation.....	33
Kazuki Nomoto, Tomo Ohsawa, Masataka Satoh, and Tohru Nakamura	
Power Performance of AlGaIn/GaN HEMT's Grown on 6" Si Substrates.....	39
Joff Derluyn, Jo Das, Kai Cheng, Anne Lorenz, Domenica Visalli, Stefan Degroote, Marianne Germain, and Staf Borghs	

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Table of Contents

[More information](#)

MOVPE Growth and Characterization of AlInN FET Structures on Si(111)	45
Christoph Hums, Aniko Gadanez, Armin Dadgar, Jürgen Bläsing, Hartmut Witte, Thomas Hempel, Annette Dietz, Pierre Lorenz, Stefan Krischok, Jürgen Alois Schaefer, Jürgen Christen, and Alois Krost	
Growth of AlGaN/GaN HEMTs on Silicon Substrates by MBE	51
Fabrice Semon, Yvon Cordier, Franck Natali, Arnaud Le Louarn, Stéphane Vézian, Sylvain Joblot, Sébastien Chenot, Nicolas Baron, Eric Frayssinet, Jean-Christophe Moreno, and Jean Massies	
Growth of AlGaN/GaN HEMTs on 3C-SiC/Si(111) Substrates	57
Yvon Cordier, Marc Portail, Sébastien Chenot, Olivier Tottreau, Marcin Zielinski, and Thierry Chassagne	
Epitaxial Growth of High-κ Dielectrics for GaN MOSFETs	63
Jesse S. Jur, Ginger D. Wheeler, Matthew T. Veety, Daniel J. Lichtenwalner, Douglas W. Barlage, and Mark A.L. Johnson	

***GaN BASED OPTICAL DEVICES
ON SILICON***

* Integrated Optics Utilizing GaN-Based Layers on Silicon Substrates	71
Armand Rosenberg, Michael A. Mastro, Joshua D. Caldwell, Ronald T. Holm, Richard L. Henry, Charles R. Eddy, Konrad Bussmann, and Mijin Kim	
Effect of Si and Er Co-Doping on Green Electroluminescence From GaN:Er ELDs	83
Rui Wang and Andrew J. Steckl	

*Invited Paper

Cambridge University Press

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Table of Contents

[More information](#)**MOVPE of m-plane InGaN/GaN Buffer and LED Structures
on γ -LiAlO₂.....89**H. Behmenburg, C. Mauder, L. Rahimzadeh Khoshroo,
T.C. Wen, Y. Dikme, M.V. Rzhetskii, E.V. Lutsenko,
G.P. Yablonskii, M.M.C. Chou, J. Voitok, M. Heuken,
H. Kalisch, and R.H. Jansen**Strong Light-Matter Coupling in GaN-Based Microcavities
Grown on Silicon Substrates.....95**Fabrice Semond, Ian Roberts Sellers, Nadège Ollier,
Franck Natali, Declan Byrne, François Réveret,
Flavian Stokker-Cheregi, Katarzyna Bejtka,
Maximo Gurioli, Anna Vinattieri, Aimé Vasson,
Pierre Disseix, Joël Leymarie, Mathieu Leroux,
and Jean Massies**AlGaN/GaN Multiple Quantum Wells Grown by Using
Atomic Layer Deposition Technique.....101**Ming-Hua Lo, Zhen-Yu Li, Shih-Wei Chen,
Jih-Cang Hong, Ting-Chang Lu, Hao-Chung Kuo,
and Shing-Chung Wang**High Optical Quality GaN Nanopillars Grown on (111) Si
Using Molecular Beam Epitaxy.....107**Agam Prakash Vajpeyi, G. Tsiakatouras,
A. Adikimenakis, K. Tsagaraki, M. Androulidaki,
and Alexandros Georgakilas***GaN AND RELATED ALLOYS ON
SILICON GROWTH AND
INTEGRATION TECHNIQUES*****Effect of Graded Al_xGa_{1-x}N Interlayer Buffer on the Strain
of GaN Grown on Si (111) Using MOCVD Method.....117**KungLiang Lin, Edward-Yi Chang, Tingkai Li,
Wei-Ching Huang, Yu-Lin Hsiao, Douglas Tweet,
Jer-shen Maa, and Sheng-Teng Hsu**Growth Optimization for High Quality GaN Films Grown
by Metal-Organic Chemical Vapor Deposition.....123**Jung Hun Jang, A.M. Herrero, Seungyoung Son,
B. Gila, C. Abernathy, and V. Craciun

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Table of Contents

[More information](#)

Investigation of Blistering Phenomena in Hydrogen-Implanted GaN and AlN for Thin-Film Layer Transfer Applications	129
R. Singh, R. Scholz, S.H. Christiansen, and U. Goesele	
Dependence of GaN Defect Structure on the Growth Temperature of the AlN Buffer Layer	135
Yuen-Yee Wong, Edward Yi Chang, Tsung-Hsi Yang, Jet-Rung Chang, Yi-Cheng Chen, and Jui-Tai Ku	
Molecular Beam Epitaxy of AlN Layers on Si (111)	141
Jean-Christophe Moreno, Eric Frayssinet, Fabrice Semond, and Jean Massies	
AlGaN Transition Layers on Si (111) Substrates—Observations of Microstructure and Impact on Material Quality	147
John C. Roberts, James W. Cook Jr., Pradeep Rajagopal, Edwin L. Piner, and Kevin J. Linthicum	
Effects of Stress-Relieving AlN Interlayers in GaN-on-Si Grown by Plasma-Assisted Molecular Beam Epitaxy	153
Adam Adikimenakis, Suman-Lata Sahonta, George Dimitrakopoulos, Jaroslav Domagala, Philomela Komninou, and Alexander Georgakilas	
InGaN Thin Films Grown by ENABLE and MBE Techniques on Silicon Substrates	159
Lothar A. Reichertz, Kin Man Yu, Yi Cui, Michael E. Hawkrige, Jeffrey W. Beeman, Zuzanna Liliental-Weber, Joel W. Ager III, Wladyslaw Walukiewicz, William J. Schaff, Todd L. Williamson, and Mark A. Hoffbauer	
InGaN Growth with Indium Content Controlled by GaN Growth Plane	165
Hisashi Kanie and Kenichi Akashi	
Electron Traps in n-GaN Grown on Si (111) Substrates by MOVPE	171
Tsuneo Ito, Yutaka Terada, and Takashi Egawa	

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Materials Research society Symposium proceedings: volume 1068

Editors: Tingkai Li, Joan M. Redwing, Michael Mastro, Edwin L. Piner and Armin Dadgar

Table of Contents

[More information](#)**The Influence of Growth Temperature on Oxygen
Concentration in GaN Buffer Layer 177**Ewa Dumiszewska, Wlodek Strupinski, Piotr Caban,
Marek Wesolowski, Dariusz Lenkiewicz,
Rafal Jakiela, Karolina Pagowska, Andrzej Turos,
and Krzysztof Zdunek**CONVENTIONAL III-V MATERIALS
AND DEVICES ON SILICON***** Formation of III-V Semiconductor Engineered Substrates
Using Smart Cut™ Layer Transfer Technology 185**
Fabrice Letertre*** Transistor Level Integration of Compound Semiconductor
Devices and CMOS (CoSMOS) 197**
Kenneth Elliott, Pamela Patterson, James C. Li,
Yakov Royter, and Tahir Hussain*** Direct Growth of III-V Devices on Silicon 203**
Katherine Herrick, Thomas Kazior, Amy Liu,
Dmitri I. Loubyshev, Joel M. Fastenau,
Miguel Urteaga, Eugene A. Fitzgerald,
Mayank T. Bulsara, David Clark, Berinder Brar,
Wonill Ha, Joshua Bergman, Nicolas Daval, and
Jeffrey LaRoche*** Epitaxial and Non-Epitaxial Heterogeneous Integration
Technologies at NGST 209**
Augusto Gutierrez-Aitken, Patty Chang-Chien,
Bert Oyama, Kelly Tornquist, Khanh Thai,
Dennis Scott, Rajinder Sandhu, Joe Zhou,
Peter Nam, and Wen Phan*** An AlGaAs/InGaAs HEMT Grown on Si Substrate with
Ge/Ge_xSi_{1-x} Metamorphic Buffer Layers 217**
Edward Yi Chang, Yueh-Chin Lin, Yu-Lin Hsiao,
Y.C. Hsieh, Chia-Yuan Chang, Chien-I. Kuo, and
Guang-Li Luo

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Editors: Tingkai Li, Joan M. Redwing, Michael Mastro, Edwin L. Piner and Armin Dadgar

Table of Contents

[More information](#)

* Epitaxial Growth of III-V Nanowires on Group IV Substrates	223
Erik Bakkers, Magnus Borgstrom, and Marcel Verheijen	
Growth and Characterization of InSb Films on Si (001).....	235
Lien Tran, Julia Dobbert, Fariba Hatami, and W. Ted Masselink	
A Study of Conformal GaAs on Si Layers by Micro- Raman and Spectral Imaging Cathodoluminescence	241
Oscar Martínez, Luis Felipe Sanz, Juan Jiménez, Bruno Gérard, and Evelyn Gil-Lafon	
Epitaxial Growth of Single Crystalline Ge Films on GaAs Substrates for CMOS Device Integration.....	247
Hock-Chun Chin, Ming Zhu, Ganesh Samudra, and Yee-Chia Yeo	

**SILICON AND OTHER MATERIALS
ON SILICON**

Nondestructive Defect Measurement and Surface Analysis of 3C-SiC on Si (001) by Electron Channeling Contrast Imaging	255
Yoosuf N. Picard, Christopher Locke, Christopher L. Frewin, Rachael L. Myers-Ward, Joshua D. Caldwell, Karl D. Hobart, Mark E. Twigg, and Stephen E. Saddow	
P Implantation Effect on Specific Contact Resistance in 3C-SiC Grown on Si.....	261
Anne-Elisabeth Bazin, Jean-François Michaud, Marc Portail, Thierry Chassagne, Marcin Zielinski, Jean-Marc Lecoq, Emmanuel Collard, and Daniel Alquier	
Simulation of Forescattered Electron Channeling Contrast Imaging of Threading Dislocations Penetrating SiC Surfaces.....	267
Mark E. Twigg, Yoosuf N. Picard, Joshua D. Caldwell, Charles R. Eddy, Philip G. Neudeck, Andrew J. Trunek, and J. Anthony Powell	

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Table of Contents

[More information](#)

A Comprehensive Study of Growth Techniques and Characterization of Epitaxial $\text{Ge}_{1-x}\text{C}_x$ (111) Layers Grown Directly on Si (111) for MOS Applications	273
Mustafa Jamil, Joseph P. Donnelly, Se-Hoon Lee, Davood Shahrjerdi, Tarik Akyol, Emanuel Tutuc, and Sanjay K. Banerjee	
Condensation Mechanism for the Formation of Relaxed SiGe Layer Grown-on-Insulator	279
Hun-Joo Lee, Gon-Sub Lee, Young-Soo Han, Seuck-Hoon Hong, Tae-Hun Shim, and Jae-Gun Park	
Author Index	285
Subject Index	289